

KSA910

PNP EPITAXIAL SILICON TRANSISTOR

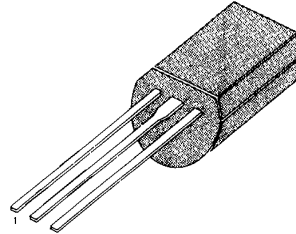
DRIVER STAGE OF AUDIO AMPLIFIER HIGH VOLTAGE SWITCHING APPLICATIONS

- Complement to KSC2310
- Collector-Emitter Voltage $V_{CE0} = -150V$
- Output Capacitance: $C_{OB} = 5pF$ (MAX)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-150	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-50	mA
Collector Dissipation	P_C	800	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ C$

TO-92L



1. Emitter 2. Collector 3. Base

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -100\mu A, I_E = 0$	-150			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -5mA, I_B = 0$	-150			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -150V, I_E = 0$			-100	nA
DC Current Gain	h_{FE}	$V_{CE} = -5V, I_C = -10mA$	40		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.8	V
Current-Gain-Bandwidth Product	f_T	$V_{CE} = -30V, I_C = -10mA$		100		MHz
Output Capacitance	C_{OB}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			5	pF

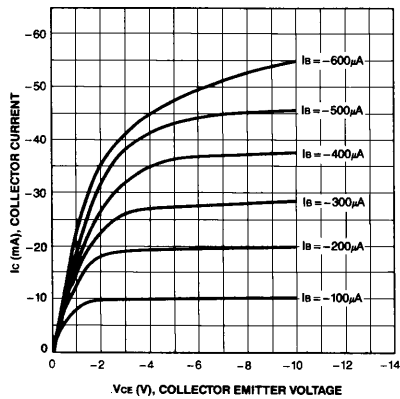
h_{FE} CLASSIFICATION

Classification	R	O	Y
h_{FE}	40-80	70-140	120-240

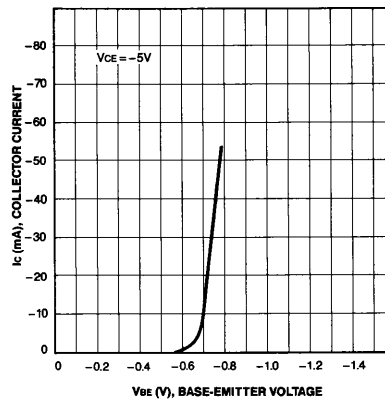
SAMSUNG

ELECTRONICS

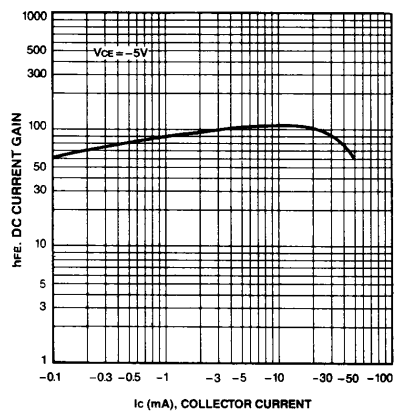
STATIC CHARACTERISTIC



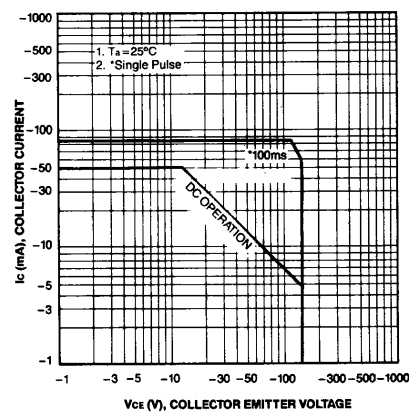
BASE-EMITTER ON VOLTAGE



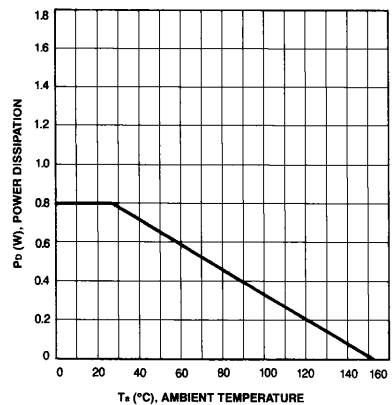
DC CURRENT GAIN



SAFE OPERATING AREA



POWER DERATING

COLLECTOR-EMITTER SATURATION VOLTAGE.
BASE-EMITTER SATURATION VOLTAGE.